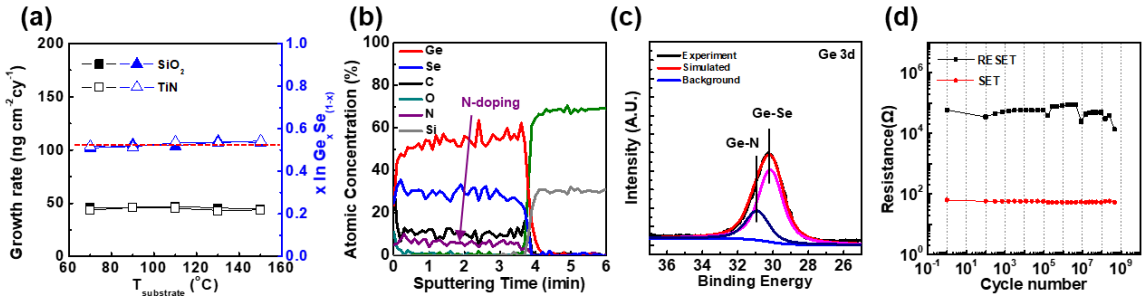

Figure 1. (a) ALD window using $Ge^{II}N(CH_3)_2[(N^iPr)_2CN(CH_3)_2]$ and $[(CH_3)_3Si]_2Se$ with an NH_3 co-reagent. (b)-(c) AES and XPS analysis for confirming the nitrogen doping. (d) Endurance cycle test of the OTS device based on N-doped GeSe.

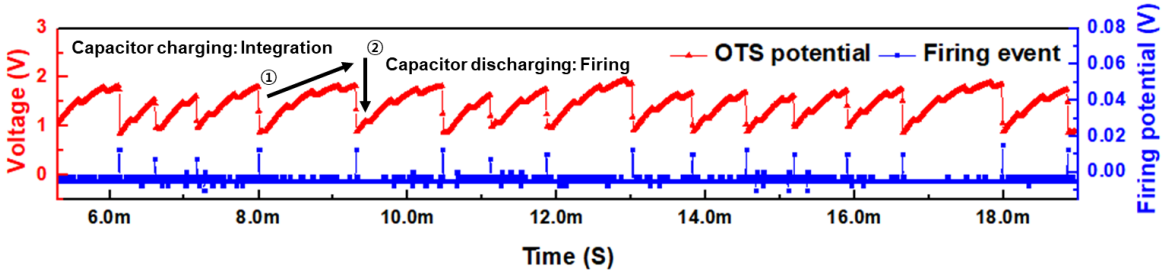

Figure 2. Output neuron firing event of leaky-integrate-and-fire neuron based on N-doped GeSe.